

## Radiation-Hardened 8-Channel Level Translator with cold sparing

### 1 GENERAL DESCRIPTION

The **AF54RHC804** is a radiation-hardened by design **8-channel level translator with 3-state outputs** that is ideally suited for space, medical imaging and other applications demanding radiation tolerance and high reliability. It is fabricated in a 180 nm CMOS process utilizing proprietary radiation-hardening techniques, delivering high resiliency to single-event effects (SEE) and to a total ionizing dose (TID) to **300 krad (Si)**.

This device is a member of the Apogee Semiconductor **AF54RHC logic family**. All members of this family operate across a full **1.4 V to 5.5 V** range providing the system designer flexibility in logic-level interfaces. The AF54RHC804 can operate across this range on both of its supply voltage inputs,  $V_{CCA}$  and  $V_{CCY}$ .

An output enable control pin allows the outputs to be placed in a high impedance (high-Z) state, simplifying usage in applications with shared busses or mixed power domains. Additionally, the outputs are placed in high-Z when  $V_{CCA}$  or  $V_{CCY}$  is not present, ensuring that no loading or leakage paths are experienced at the output nodes when the input rail is not powered.

Zero-power penalty™ cold sparing is supported, along with Class 1C ESD protection on all inputs and outputs. A proprietary output stage and robust power-on reset (POR) circuit allow the AF54RHC804 to be cold-spared in any redundant configuration with no static power loss on any pad of the device. The redundant output stage also features a high drive capability with low static power loss.

The AF54RHC804 also features a triple-redundant design throughout its entire circuitry, which allows it to be immune to single-event transients (SET) without requiring additional redundant devices.

Ordering information may be found in Table 10 on Page 14.

### 1.1 FEATURES

- 1.4 VDC to 5.5 VDC operation
- Inputs tolerant up to 5.5 VDC at any  $V_{CCA}$
- Provides logic-level translation to  $V_{CCY}$
- Extended operating temperature range (-55 °C to +125 °C)
- Proprietary **cold sparing capability** with **zero** static power penalty
- **Built-in triple redundancy** for enhanced reliability
- Tri-state output drivers
- Class 1C ESD protection (1000 V HBM, 500 V CDM)
- TID resilience of **300 krad (Si)**.
- SEL immune to LET of **75 MeV-cm<sup>2</sup>/mg**
- Meets NASA's ASTM E595 outgassing specification

### 1.2 LOGIC DIAGRAM

The AF54RHC804 logic function is shown below:

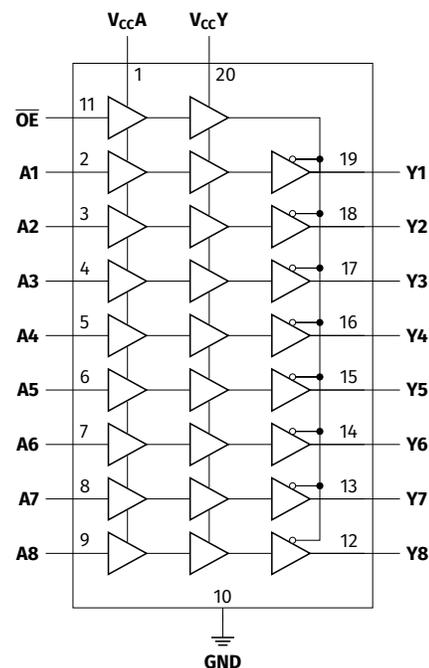


Figure 1: AF54RHC804 Logic Diagram

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## 2 ACRONYMS AND ABBREVIATIONS

ESD	Electrostatic Discharge
POR	Power On Reset
RHA	Radiation Hardness Assurance
SEE	Single Event Effects
SEL	Single Event Latchup
SET	Single Event Transient
TID	Total Ionizing Dose
TMR	Triple Modular Redundancy
CDM	Charged-device Model
HBM	Human-body Model

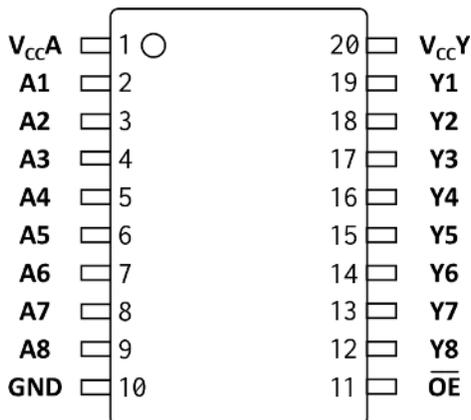
### 3 LOGIC DATA

The AF54RHC804 truth table is found in Table 1. **H** indicates HIGH logic level, **L** indicates LOW logic level, **X** indicates DON'T CARE and **Z** indicates HIGH-Z (TRI-STATE). Subscript **n** reflects one of the eight buffers in the device (1 to 8).

**Table 1:** AF54RHC804 Device Truth Table

Inputs		Output
$\overline{OE}$	$A_n$	$Y_n$
L	L	L
L	H	H
H	X	Z

## 4 PIN CONFIGURATION



**Figure 2:** AF54RHC804 Device Pinout

**Table 2:** AF54RHC804 Device Pinout

PIN NAME(S)	PIN NUMBER(S)	DESCRIPTION
A1 A2 A3 A4 A5 A6 A7 A8	2 3 4 5 6 7 8 9	Signal Inputs. Referenced to V <sub>CC</sub> A.
Y1 Y2 Y3 Y4 Y5 Y6 Y7 Y8	19 18 17 16 15 14 13 12	Signal Outputs. Referenced to V <sub>CC</sub> Y.
$\overline{OE}$	11	Output Enable (active-low). Referenced to V <sub>CC</sub> A.
V <sub>CC</sub> A	1	Positive Voltage Supply (A Side)
V <sub>CC</sub> Y	20	Positive Voltage Supply (Y Side)
GND	10	Ground

## 5 ELECTRICAL CHARACTERISTICS

The sign convention for current follows JEDEC standards with negative values representing current sourced from the device and positive values representing current sunk into the device.

### 5.1 ABSOLUTE MAXIMUM RATINGS

Excursions beyond the values listed in Table 3 may cause permanent damage to the device. Proper function of the device cannot be guaranteed if these values are exceeded, and long-term device reliability may be affected. Functionality of the device at these values, or beyond those listed in [Recommended Operating Conditions](#) (Table 4) is not guaranteed.

All parameters are specified across the entire operating temperature range unless otherwise specified.

**Table 3:** Absolute Maximum Ratings

SYMBOL	PARAMETER	VALUE	UNITS
$V_{CCA}, V_{CCY}$	Supply Voltage	-0.5 to +5.5	V
$V_I$	Input voltage range	-0.5 to +5.5	V
$V_O$	Output voltage range	-0.5 to $V_{CCY} + 0.5^{(1)}$	V
$I_{IK} (V_I < 0)$	Input clamp current	100	mA
$I_O$	Continuous output current (per pin)	100	mA
$I_{CC}$	Maximum supply current	100	mA
$V_{ESD}$	ESD Voltage	HBM	1000
		CDM	500
$T_J$	Operating junction temperature range	-55 to +150	°C
$T_{STG}$	Storage temperature range	-65 to +150	°C

<sup>(1)</sup>  $V_O$  must remain below absolute maximum rating of  $V_{CCA}, V_{CCY}$

**5.2 RECOMMENDED OPERATING CONDITIONS**

All recommended parameters below are specified across the entire operating temperature range unless otherwise specified.

**Table 4:** Recommended Operating Conditions

SYMBOL	PARAMETER	MIN	MAX	UNITS	
$V_{CCA}, V_{CCY}$	Supply voltage	1.4	5.5	V	
$V_I$	Input voltage range	0	5.5	V	
$V_O$	Output voltage range	0	$V_{CCY}$	V	
$V_{IH}$	HIGH-level input voltage	$V_{CCA} = 1.4$ to $1.6$ V	1.12	-	V
		$V_{CCA} = 1.65$ to $1.95$ V	1.4	-	
		$V_{CCA} = 2.3$ to $2.7$ V	1.9	-	
		$V_{CCA} = 3.0$ to $3.6$ V	2.5	-	
		$V_{CCA} = 4.5$ to $5.5$ V	3.8	-	
$V_{IL}$	LOW-level input voltage	$V_{CCA} = 1.4$ to $1.6$ V	-	0.32	V
		$V_{CCA} = 1.65$ to $1.95$ V	-	0.4	
		$V_{CCA} = 2.3$ to $2.7$ V	-	0.6	
		$V_{CCA} = 3.0$ to $3.6$ V	-	0.9	
		$V_{CCA} = 4.5$ to $5.5$ V	-	1.35	
$I_{OH}$	HIGH-level output current	$V_{CCY} = 1.4$ to $1.6$ V	-	-2	mA
		$V_{CCY} = 1.65$ to $1.95$ V	-	-4	
		$V_{CCY} = 2.3$ to $2.7$ V	-	-8	
		$V_{CCY} = 3.0$ to $3.6$ V	-	-16	
		$V_{CCY} = 4.5$ to $5.5$ V	-	-24	
$I_{OL}$	LOW-level output current	$V_{CCY} = 1.4$ to $1.6$ V	-	2	mA
		$V_{CCY} = 1.65$ to $1.95$ V	-	4	
		$V_{CCY} = 2.3$ to $2.7$ V	-	8	
		$V_{CCY} = 3.0$ to $3.6$ V	-	16	
		$V_{CCY} = 4.5$ to $5.5$ V	-	24	
$t_r, t_f$	Input rise or fall time (10% - 90%)	$V_{CCA} = 1.4$ to $1.6$ V	-	2000	ns
		$V_{CCA} = 1.65$ to $1.95$ V	-	1000	
		$V_{CCA} = 2.3$ to $2.7$ V	-	600	
		$V_{CCA} = 3.0$ to $3.6$ V	-	500	
		$V_{CCA} = 4.5$ to $5.5$ V	-	400	

**Table 5:** Thermal Information

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS
$T_J$	Operating junction temperature	-55	-	+125	°C
$R_{\theta JA}$	Junction to ambient thermal resistance	-	100	-	°C/W

**5.3 STATIC CHARACTERISTICS**

All parameters are specified across the entire operating temperature range unless otherwise specified.

**Table 6:** DC Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	V <sub>CCY</sub>	MIN	TYP	MAX	UNITS		
V <sub>OL</sub>	LOW-Level Output Voltage <sup>(1)</sup>	I <sub>O</sub> = 100 μA	1.4 to 5.5 V	-	0.02	0.05	V		
		I <sub>O</sub> = 1 mA	1.4 to 5.5 V	-	0.05	0.15	V		
		I <sub>O</sub> = 2 mA	1.4 V	-	0.18	0.4	V		
		I <sub>O</sub> = 4 mA	1.65 V	-	0.27	0.8	V		
			2.3 V	-	0.3	0.6	V		
			3.0 V	-	0.2	0.4	V		
			4.5 V	-	0.2	0.4	V		
		I <sub>O</sub> = 8 mA	2.3 V	-	0.6	1.0	V		
			3.0 V	-	0.4	0.8	V		
			4.5 V	-	0.3	0.6	V		
		I <sub>O</sub> = 16 mA	3.0 V	-	1.0	1.4	V		
			4.5 V	-	1.1	1.2	V		
I <sub>O</sub> = 24 mA	4.5 V	-	1.1	1.5	V				
V <sub>OH</sub>	HIGH-Level Output Voltage <sup>(1)</sup>	I <sub>O</sub> = -100 μA	1.4 to 5.5 V	V <sub>CCY</sub> - 0.1	V <sub>CCY</sub> - 0.02	-	V		
		I <sub>O</sub> = -1 mA	1.4 to 5.5 V	V <sub>CCY</sub> - 0.15	V <sub>CCY</sub> - 0.08	-	V		
		I <sub>O</sub> = -2 mA	1.4 V	0.9	1.2	-	V		
		I <sub>O</sub> = -4 mA	1.65 V	1	1.35	-	V		
			2.3 V	1.8	2.0	-	V		
			3.0 V	2.6	2.7	-	V		
			4.5 V	4.2	4.4	-	V		
		I <sub>O</sub> = -8 mA	2.3 V	1.4	1.7	-	V		
			3.0 V	2.2	2.5	-	V		
			4.5 V	3.9	4.1	-	V		
		I <sub>O</sub> = -16 mA	3.0 V	1.5	2.0	-	V		
			4.5 V	3.3	3.8	-	V		
		I <sub>O</sub> = -24 mA	4.5 V	3.0	3.5	-	V		
		I <sub>CCY</sub>	Quiescent supply current	V <sub>I</sub> = V <sub>CCA</sub> or GND OE = GND I <sub>O</sub> = 0 mA	5.5 V	-	75	200	μA
		SYMBOL	PARAMETER	CONDITIONS	V <sub>CCA</sub>	MIN	TYP	MAX	UNITS
		I <sub>I</sub>	Input current	V <sub>I</sub> = V <sub>CCA</sub> or GND	1.4 to 5.5 V	-	-	±8	μA
I <sub>OZ</sub>	Output leakage current <sup>(2)</sup>	V <sub>I</sub> = V <sub>CCY</sub> or GND OE = V <sub>CCA</sub>	1.4 to 5.5 V	-	-	±2.5	μA		
I <sub>OFF</sub>	Powerdown leakage current <sup>(2,3)</sup>	V <sub>I</sub> = GND to 5.5 V	OFF	-	-	8	μA		
I <sub>CCA</sub>	Quiescent supply current	V <sub>I</sub> = V <sub>CCA</sub> or GND I <sub>O</sub> = 0 mA	5.5 V	-	30	100	μA		

<sup>(1)</sup> V<sub>CCA</sub> = 1.4 to 5.5 V for these conditions

<sup>(2)</sup> V<sub>CCY</sub> = 0 to 5.5 V for these conditions

<sup>(3)</sup> V<sub>CCA</sub> is at GND potential

### 5.4 DYNAMIC CHARACTERISTICS

All parameters are specified across the entire operating temperature range unless otherwise specified.

**Table 7:** AC Electrical Characteristics.  $C_L = 50$  pF

Symbol	Parameter	$V_{CCA}$	$V_{CCY}$										Units
			1.5 ±0.1 V		1.8 ±0.15 V		2.5 ±0.2 V		3.3 ±0.3 V		5 ±0.5 V		
			TYP	MAX	TYP	MAX	TYP	MAX	TYP	MAX	TYP	MAX	
$t_{pd}^{(1)}$	Propagation Delay (Input <b>A</b> to Output <b>Y</b> )	1.5 ±0.1 V	24.5	60	15.6	41	10.6	23	8.9	20	8.2	18	ns
		1.8 ±0.15 V	18.5	60	11.8	25	7.9	15	6.2	13	5.8	11	ns
		2.5 ±0.2 V	18	60	11.3	25	7.4	15	5.6	13	4.3	11	ns
		3.3 ±0.3 V	17.8	60	11.2	25	7.2	15	5.4	13	4.2	11	ns
		5 ±0.5 V	17.7	60	11.1	25	7.1	15	5.3	13	3.9	11	ns
$t_{dis}^{(2)}$	Output Disable Time (Input <b>OE</b> to Output <b>Y</b> )	1.5 ±0.1 V	30.1	45	25.9	40	22.6	37	21.8	35	21.8	33	ns
		1.8 ±0.15 V	27.3	80	18.3	53	17.2	41	17.1	35	18.2	25	ns
		2.5 ±0.2 V	26.8	80	17.9	53	16.7	41	16.3	35	16.2	25	ns
		3.3 ±0.3 V	26.1	80	17.7	53	16.6	41	16.1	35	15.9	25	ns
		5 ±0.5 V	26	80	17.7	53	16.5	41	16.1	35	15.9	25	ns
$t_{en}^{(3)}$	Output Enable Time (Input <b>OE</b> to Output <b>Y</b> )	1.5 ±0.1 V	56.5	91	38.6	69	24.4	42	20.9	36	19.3	31	ns
		1.8 ±0.15 V	47	80	21.7	53	17.3	41	15.5	35	15.1	25	ns
		2.5 ±0.2 V	46.5	80	21.4	53	16.9	41	15.0	35	13.7	25	ns
		3.3 ±0.3 V	46.3	80	21.3	53	16.8	41	14.9	35	13.5	25	ns
		5 ±0.5 V	46.4	80	21.4	53	17.0	41	15.0	35	13.6	25	ns

(1) equivalent to  $t_{PLH}$ ,  $t_{PHL}$

(2) equivalent to  $t_{PLZ}$ ,  $t_{PHZ}$

(3) equivalent to  $t_{PZL}$ ,  $t_{PZH}$

**Table 8:** AC Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	$V_{CCY}$	MIN	TYP	MAX	UNITS
$t_{sk}$	Channel-to-channel skew	$C_L = 50$ pF	1.4 to 5.5 V	-	-	1	ns
$C_{in}$	Input Capacitance <sup>(1)</sup>	$V_I = V_{CC}$ or GND	1.4 to 5.5 V	-	2	4	pF
$C_{pd}$	Power Dissipation Capacitance <sup>(1)</sup>	$I_O = 0$ mA, $f = 1$ MHz	5.5 V	-	40	-	pF

(1) guaranteed by design

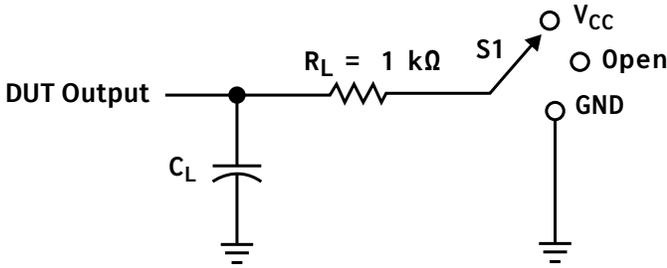
### 5.5 RADIATION RESILIENCE

For detailed radiation testing reports, please contact Apogee Semiconductor at [sales@apogeesemi.com](mailto:sales@apogeesemi.com).

**Table 9:** Radiation Resilience Characteristics

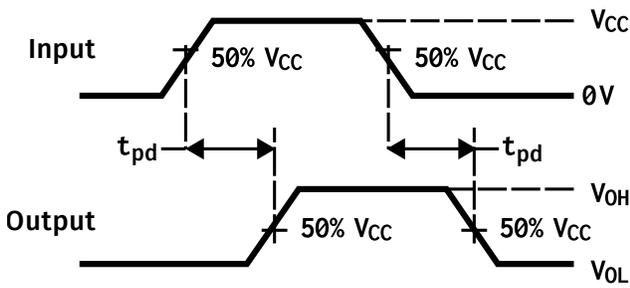
PARAMETER	CONDITIONS	VALUE	UNITS
Total Ionizing Dose (TID)	Please contact Apogee Semiconductor for test report.	300	krad (Si)
SEL Onset LET Threshold	Please contact Apogee Semiconductor for test report.	≥75	MeV-cm <sup>2</sup> /mg

**5.6 CHARACTERISTICS MEASUREMENT INFORMATION**

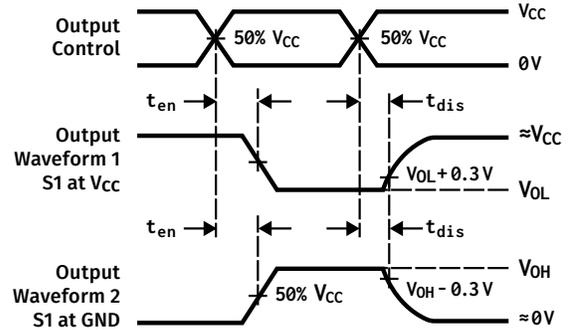


**Figure 3:** Load Circuit for 3-State Outputs

TEST	S1
$t_{pd}$	GND
$t_{PLZ}, t_{PZL}$	$V_{CC}$
$t_{PHZ}, t_{PZH}$	GND



**Figure 4:** Propagation Delay Measurement



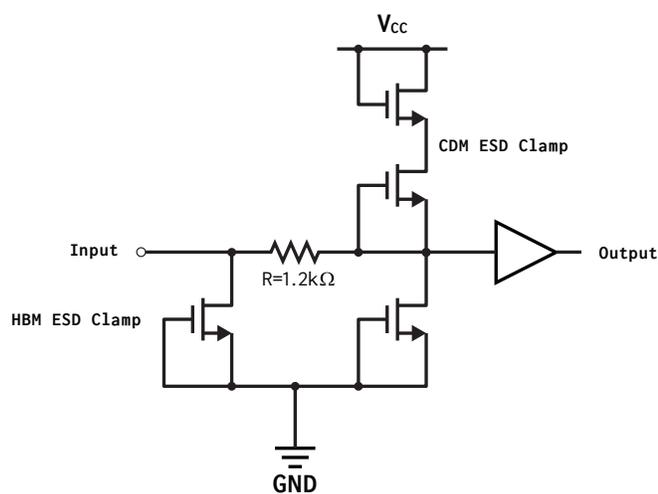
**Figure 5:** Enable and Disable Time Measurements

## 6 DETAILED DESCRIPTION

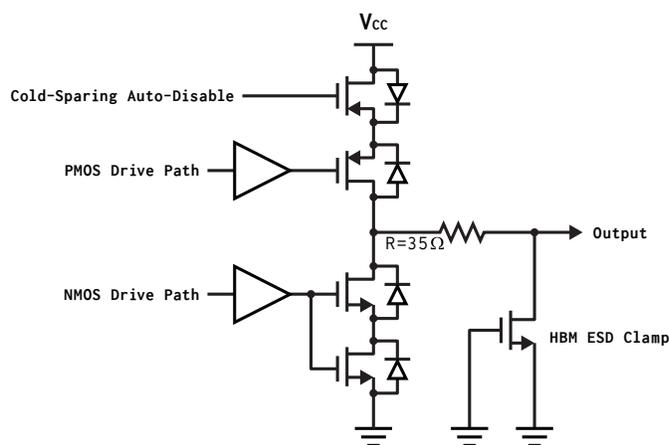
The AF54RHC804 is a 8-channel level translator with 3-state outputs designed to operate from a wide supply voltage of 1.4 to 5.5 V with fully redundant input and output stages, providing for superior radiation resilience.

The output and input stages are constructed with transient-activated clamps (Figure 6, 7) that prevent inadvertent biasing of the  $V_{CC}$  power rail through parasitic diodes inherent to conventional input, output, and ESD circuits. The IC also incorporates an internal power-on reset (POR) circuit guaranteeing correct operation at power supply voltages as low as 1.4V.

The AF54RHC family's I/O protection circuitry allows for cold sparing configurations as it avoids a leakage current penalty on inputs and outputs while in a power-down state. This can result in considerable power savings in systems where multiple-path redundancy is employed. The ESD clamp circuits for this logic family are designed to support Class 1C ESD levels of 1 kV HBM and 500 V CDM.



**Figure 6:** Input Pin Structure



**Figure 7:** Output Pin Structure

## 7 APPLICATIONS INFORMATION

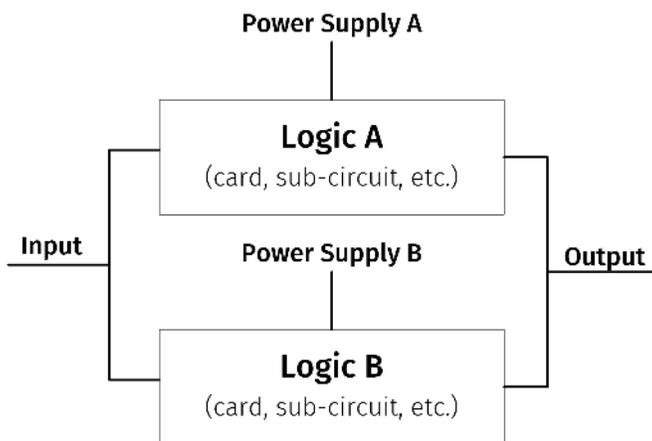
The AF54RHC804 provides a simple and robust means of interfacing digital logic between different voltage levels and domains. It can shift logic signals up from a lower voltage to a higher voltage or shift signals down from higher to lower voltages.

It offers several features that make interfacing between different domains simple. First, the absence of an input supply voltage results in a tri-state condition at the output. Second, the outputs may also be tri-stated through assertion of the  $\overline{OE}$  pin, which can be tied with power-supply enables or other control signals.

In an application utilizing a modern FPGA with 1.5 V I/O buffers that needs to interface to systems running at higher voltages (i.e. 5 V), the AF54RHC804 can be used to shift these signals to a range appropriate for the FPGA. The AF54RHC804 provides integrated triple modular redundancy (TMR), as well as SET resiliency on each buffer. In the event the 5 V supply is off, the AF54RHC804 will automatically tri-state the output buffers. The  $\overline{OE}$  pin of the device can be tied to the FPGA power-enable logic such that  $\overline{OE}$  is de-asserted when the 1.5 V I/O rail is not present.

### 7.1 APPLICATIONS EXAMPLE

As the AF54RHC family is radiation-hardened by design and includes internal TMR, it can be utilized in high-reliability applications without additional supporting circuitry or devices. Nonetheless, some application requirements call for fully-redundant designs, where an “A” and a “B” device are required, often on separate power rails.



**Figure 8:** Two-Path Cold-Sparing Configuration

With the cold sparing capability of the AF54RHC family, fully redundant “A” and “B” functions may be placed in parallel (as seen in Figure 8) running off redundant power supplies. The inputs and outputs on each one of these functions are assumed to be based on the AF54RHC family, allowing for direct parallel connection without unwanted leakage current paths during cold sparing. In the event of a failure in power supply A or within function A, the system can simply shut power supply A off and switch on power supply B, without requiring additional input or output switching or configuration changes.

## 7.2 POWER SUPPLY RECOMMENDATIONS

This device can operate at any voltage within the range specified in [Table 4 Recommended Operating Conditions](#).

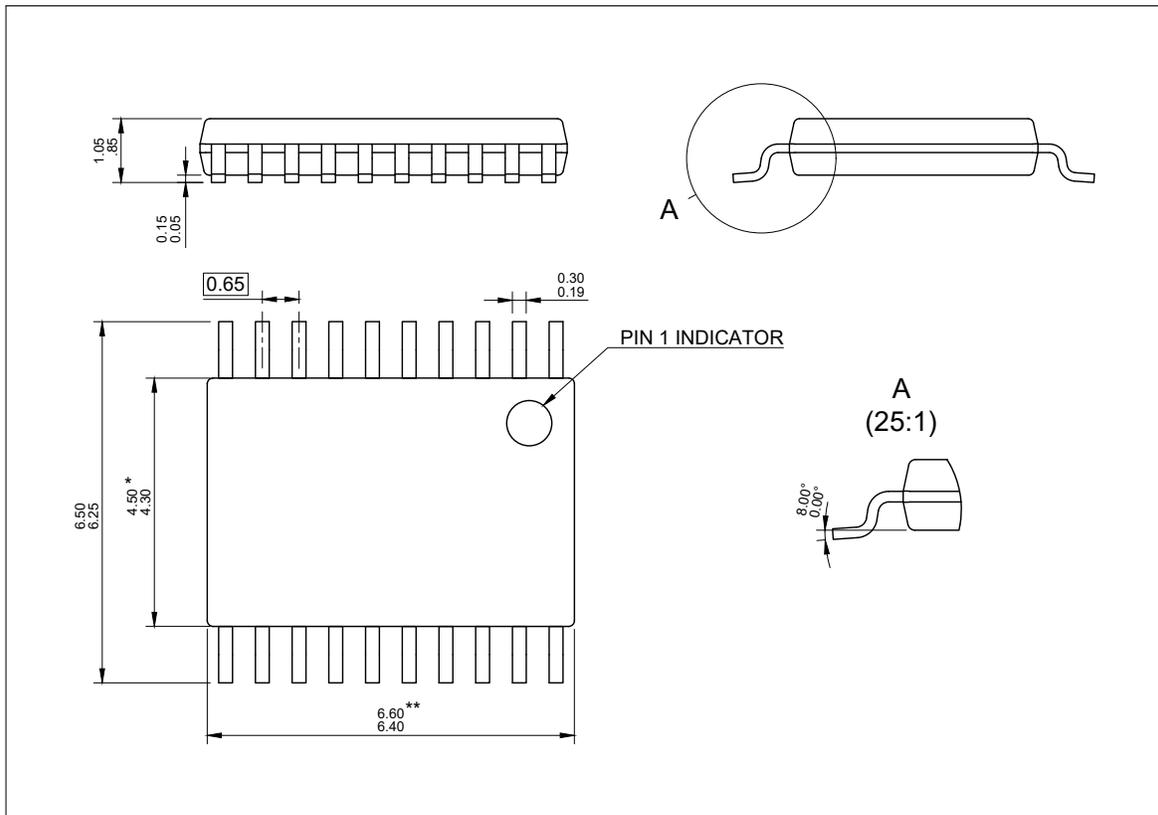
At a minimum, a 16 VDC (or higher), X7R-rated 0.1  $\mu$ F ceramic decoupling capacitor should be placed near (within 1 cm) the  $V_{CC}$  pins of the device.

## 7.3 APPLICATION TIPS

Unused **inputs** must **not** be left floating. They may be connected to either a low (GND) or high ( $V_{CCA}$ ) bias to provide a known state at the input of the device. Resistors may be used to tie off unused inputs. In the event of a design change, such resistors can be removed, thereby allowing use of the inputs without having to cut traces on the PCB.

An unused **output** may be left floating. It is suggested that it be routed to a test point or similar accessible structure in case the associated function needs to be utilized as part of a design revision.

## 8 PACKAGING INFORMATION



**Notes:**

1. All linear dimensions are in millimeters. Dimensioning and tolerancing are as per ISO/TS 128-71:2010
2. The part is compliant with JEDEC MO-153 specifications.

\* Body width does **not** include interlead flash. Interlead flash shall not exceed 0.25 mm each side.

\*\* Body length does **not** include mold flash, protrusion, or gate burrs. Mold flash, protrusions, and gate burrs shall not exceed 0.15 mm on each side.

**Figure 9:** Package Mechanical Drawing

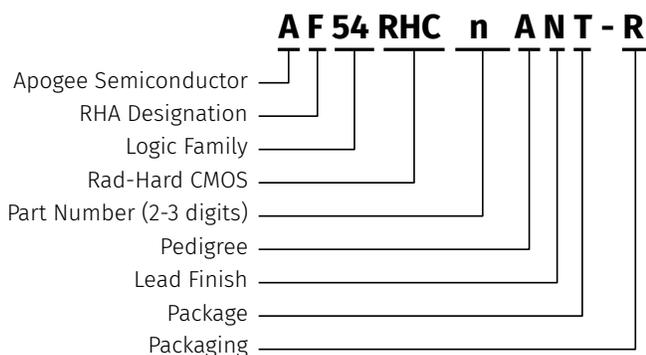
## 9 ORDERING INFORMATION

Example part numbers for the AF54RHC804 are listed in Table 10. The full list of options for this part can be found in Figure 10. For a detailed description of product grades, please refer to [Product Grades and Quality Flows document](#). Please contact Apogee Semiconductor sales at [sales@apogeesemi.com](mailto:sales@apogeesemi.com) for further information on sampling, lead time and purchasing on specific part numbers.

**Table 10:** AF54RHC804 Ordering Information

DEVICE	DESCRIPTION	PACKAGE	LEAD FINISH	PACKAGE MASS
AF54RHC804ANT-R	Rad-Hard 8-Channel Level Translator (300 krad (Si))	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804ANT-J <sup>(1)</sup>	Rad-Hard 8-Channel Level Translator (300 krad (Si))	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804BNT-R	Rad-Hard 8-Channel Level Translator (300 krad (Si))	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804BNT-J <sup>(1)</sup>	Rad-Hard 8-Channel Level Translator (300 krad (Si))	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804CNT-R	Rad-Hard 8-Channel Level Translator (300 krad (Si))	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804CNT-J <sup>(1)</sup>	Rad-Hard 8-Channel Level Translator (300 krad (Si))	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804ENT-R	Rad-Hard 8-Channel Level Translator (for eval only)	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804ENT-J <sup>(1)</sup>	Rad-Hard 8-Channel Level Translator (for eval only)	Plastic TSSOP-20	NiPdAu	73.7 mg

<sup>(1)</sup> Available through distributors only.



**Figure 10:** Part Number Decoder

- RHA Designation
  - P** 30 krad (Si)
  - F** 300 krad (Si)
- Part Number
  - \_** 804 (8-Channel Level Translator)
- Pedigree
  - A** -55 to +125 °C (Burn-in)
  - B** -55 to +125 °C (No burn-in)
  - C** 25 °C (No burn-in)
  - E** 25 °C Functional Test Only (Evaluation)
- Lead Finish
  - N** Nickel-Palladium-Gold (NiPdAu)
- Package
  - T** 20-pin Thin Shrink Small Outline Package (TSSOP)
- Packaging
  - R** Tape and Reel<sup>(1)</sup>
  - J** JEDEC Tray

<sup>(1)</sup> [Contact us](#) for custom reel quantities. Orders less than full reel quantities may be shipped as cut tape.

## 10 REVISION HISTORY

REVISION	DESCRIPTION	DATE
C02	For $V_{CCA} = 1.4$ to $1.6$ V, $V_{IH}$ limit corrected from $0.6$ V to $1.12$ V and $V_{IL}$ limit corrected from $0.25$ V to $0.32$ V. Timing parameters $t_{pd}$ , $t_{en}$ , and $t_{dis}$ updated in Table 7 for $V_{CCA} = 1.5 \pm 0.1$ V.	2025-10-31
C01	SEL onset threshold was corrected from $\geq 80$ MeV-cm <sup>2</sup> /mg to $\geq 75$ MeV-cm <sup>2</sup> /mg.	2025-08-28
C00	Initial release	2025-08-19

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